

30 V, dual P-channel Trench MOSFET 25 March 2015

Product data sheet

### 1. General description

Dual P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Low threshold voltage
- Leadless ultra small and ultra thin SMD plastic package 1.1 x 1.0 x 0.37 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

### 3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor					Ì		
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-30	V
V <sub>GS</sub>	gate-source voltage	-		-8	-	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-	-410	mA
Static characteristics (per transistor)							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C		-	1.2	1.4	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



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#### **Pinning information** 5.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	2 5	
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa260
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

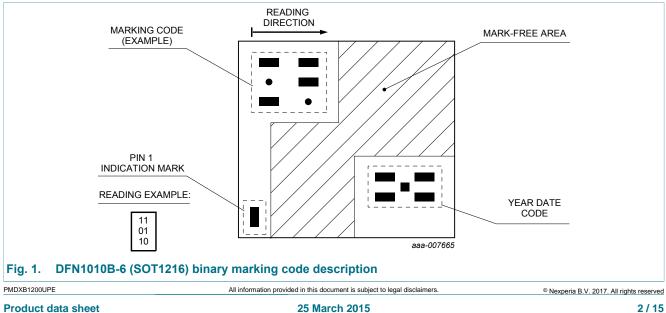
#### **Ordering information** 6.

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
PMDXB1200UPE	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

#### Marking 7.

#### Marking codes Table 4.

Type number	Marking code
PMDXB1200UPE	11 10 00



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### 8. Limiting values

#### Table 5. Limiting values

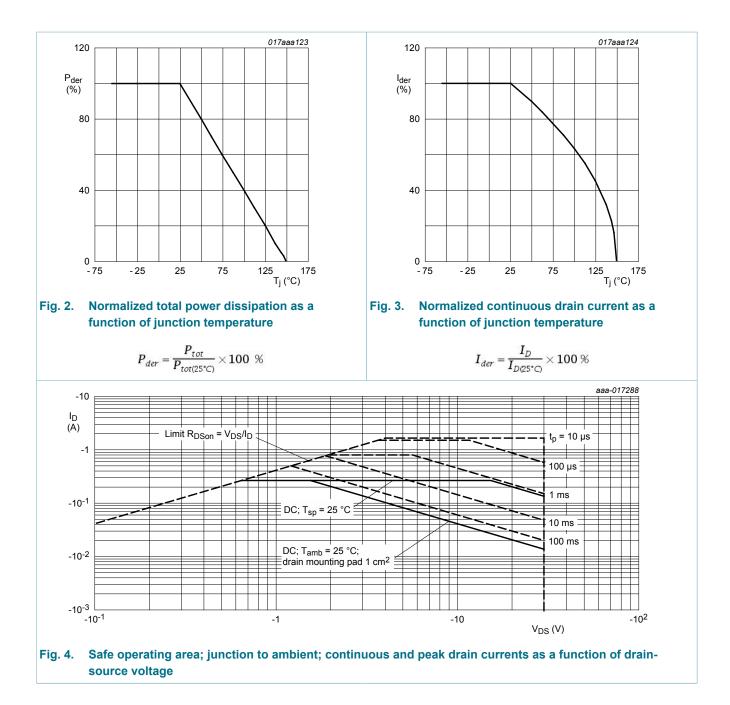
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor					_
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-30	V
V <sub>GS</sub>	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-410	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-260	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \ \mu s$		-	-1.7	А
P <sub>tot</sub> total p	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	285	mW
			[1]	-	410	mW
		T <sub>sp</sub> = 25 °C		-	4030	mW
Source-dra	in diode		1			
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	-410	mA
Per device						
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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### 9. Thermal characteristics

Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
R <sub>th(j-a)</sub> t	thermal resistance	in free air	[1]	-	380	440	K/W
from junction to ambient			[2]	-	275	305	K/W

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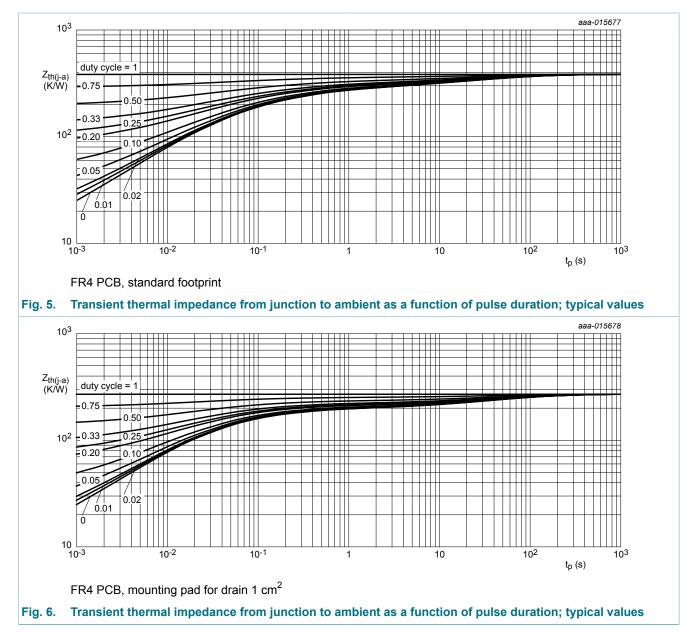
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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	27	31	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



## **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static chara	cteristics (per transistor)					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 µA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-30	-	-	V
V <sub>GSth</sub>	gate-source threshold voltage	$I_D$ = -250 µA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -30 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 8 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	5	μA
		V <sub>GS</sub> = -8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-5	μA
		$V_{GS}$ = 4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	1	μA
		$V_{GS}$ = -4.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 2.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS}$ = -2.5 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	-100	nA
R <sub>DSon</sub> drain-source of resistance	drain-source on-state	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C	-	1.2	1.4	Ω
	resistance	$V_{GS}$ = -4.5 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 150 °C	-	2	2.4	Ω
		$V_{GS}$ = -2.5 V; I <sub>D</sub> = -320 mA; T <sub>j</sub> = 25 °C	-	1.7	2.3	Ω
		V <sub>GS</sub> = -1.8 V; I <sub>D</sub> = -80 mA; T <sub>j</sub> = 25 °C	-	2.1	3.1	Ω
		V <sub>GS</sub> = -1.5 V; I <sub>D</sub> = -10 mA; T <sub>j</sub> = 25 °C	-	3	5.1	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; I <sub>D</sub> = -410 mA; T <sub>j</sub> = 25 °C	-	820	-	mS
Dynamic ch	aracteristics (per transist	or)				
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -410 mA;	-	0.7	1.2	nC
Q <sub>GS</sub>	gate-source charge	V <sub>GS</sub> = -4.5 V; T <sub>j</sub> = 25 °C	-	0.17	-	nC
Q <sub>GD</sub>	gate-drain charge		-	0.16	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	43.2	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	5.9	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	4.2	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = -15 V; I <sub>D</sub> = -410 mA;	-	3	-	ns
t <sub>r</sub>	rise time	$V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ; $T_j$ = 25 °C	-	4	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	14	-	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-drai	n diode (per transistor)		I		1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -410 mA; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	-0.95	-1.2	V

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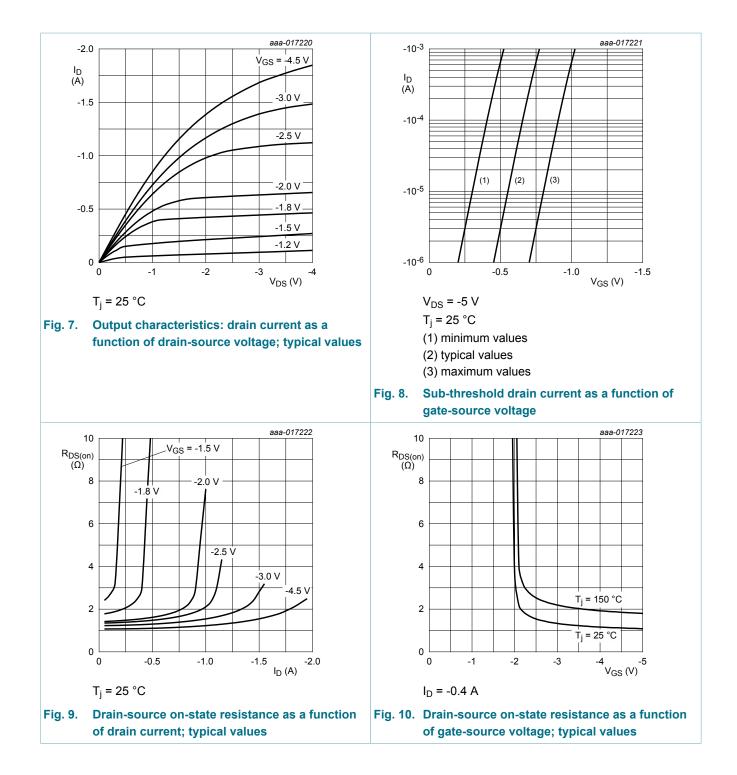
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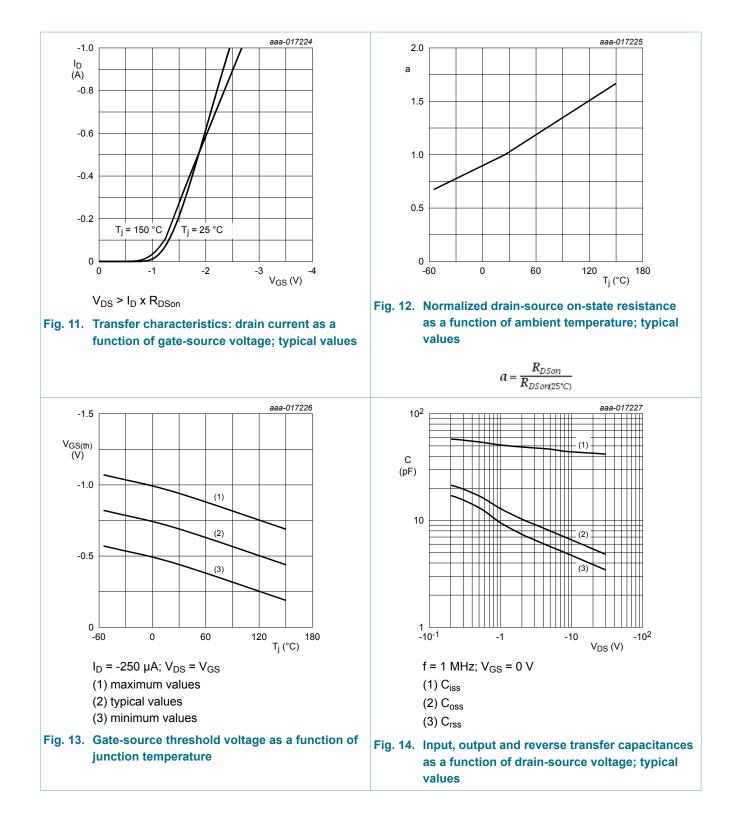


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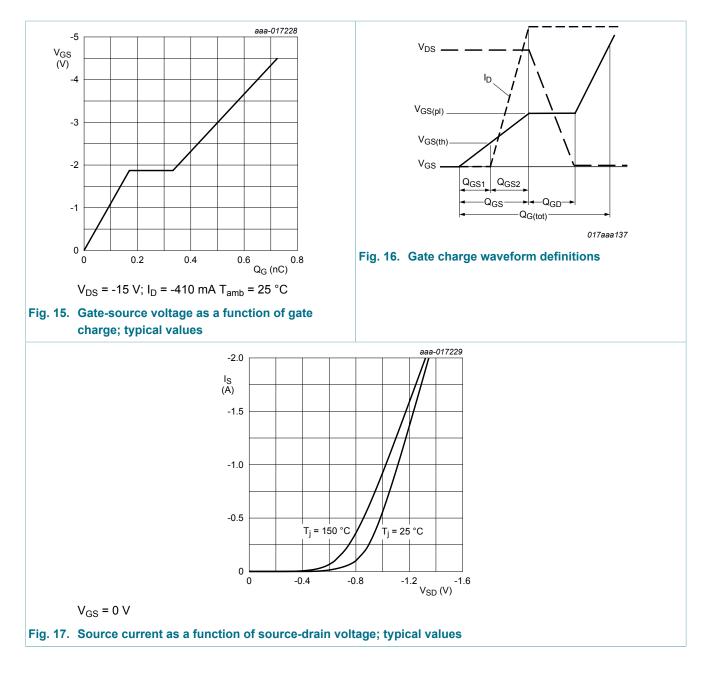
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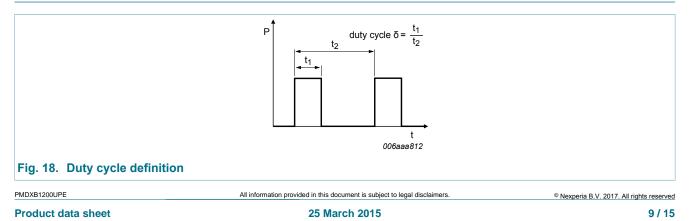
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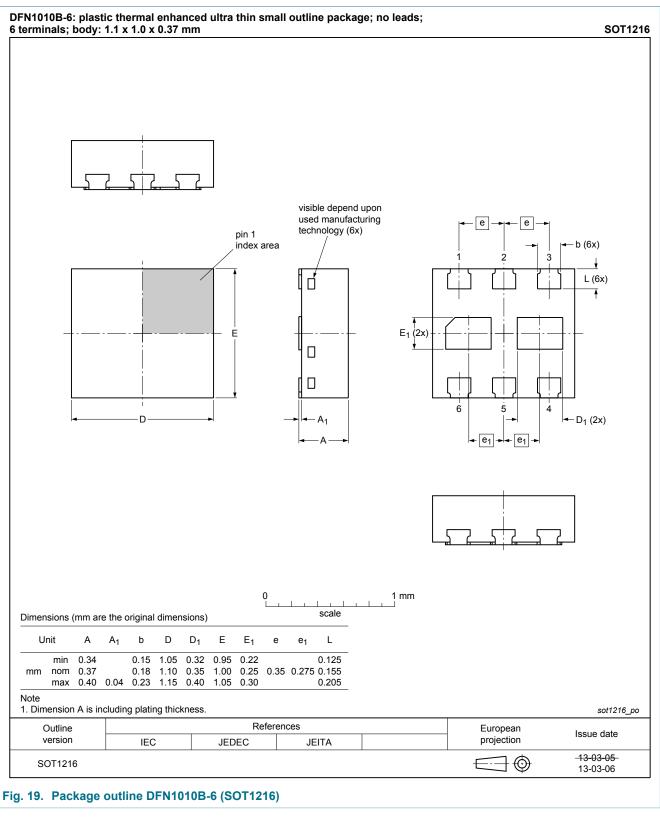


## **11. Test information**



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### 12. Package outline



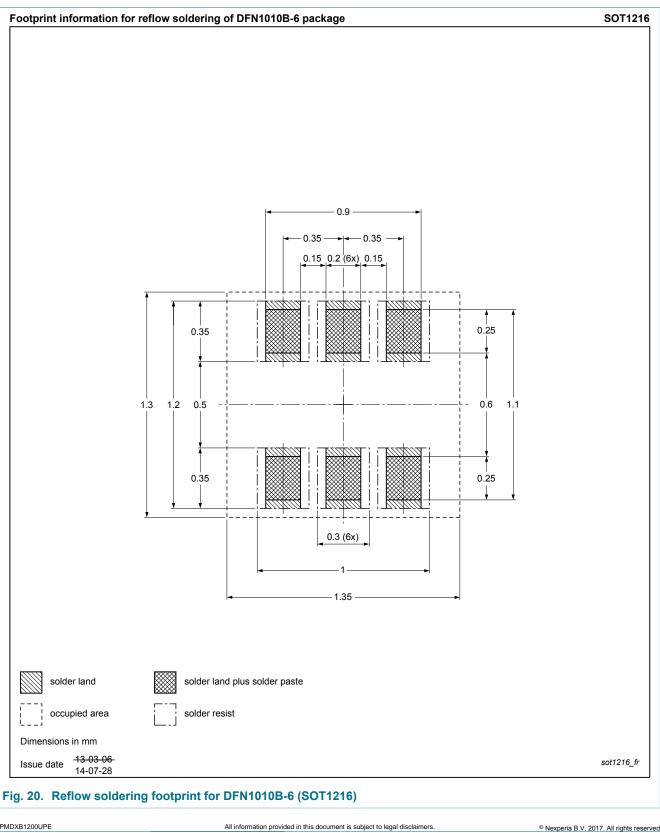
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### 13. Soldering



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## 14. Revision history

Table 8. Revision his	ble 8. Revision history					
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMDXB1200UPE v.1	20150325	Product data sheet	-	-		

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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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